

1M × 64-Bit Dynamic RAM Module

HYM 641010GS-60/-70
HYM 641020GS-60/-70

Advanced Information

- 1 048 576 words by 64-bit organization
- Fast access and cycle time
 - 60 ns access time
 - 110 ns cycle time (-60 version)
 - 70 ns access time
 - 130 ns cycle time (-70 version)
- Fast page mode capability with
 - 40 ns cycle time (-60 version)
 - 45 ns cycle time (-70 version)
- Single + 5 V (± 10 %) supply
- Low power dissipation
 - max. 9680 mW active (-60 version)
 - max. 8800 mW active (-70 version)

CMOS – 451 mW standby
TTL – 550 mW standby
- $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh, $\overline{\text{RAS}}$ -only-refresh
- Byte Write Capability
- 16 decoupling capacitors mounted on substrate
- All inputs, outputs and clock fully TTL compatible
- 4 Byte interleave enabled, Dual Address inputs (A0/B0)
- Buffered inputs except $\overline{\text{RAS}}$ and DQ
- 168 pin, dual read-out, Single in-Line Memory Module
- Utilizes sixteen 1M × 4 -DRAMs (HYB 514400BJ/BT) and four BiCMOS 8-bit buffers/line drivers 74ABT244
- Two version : HYM 641010GS with SOJ-components (8.89 mm module thickness)
HYM 641020GS with TSOPII-components (4.06 mm module thickness)
- 1024 refresh cycles / 16 ms
- Optimized for use in byte-write non-parity applications
- Gold contact pads, double sided module with 25.35 mm (1000 mil) height

The HYM 641010/20GS-60/-70 is a 8 MByte DRAM module organized as 1 048 576 words by 64-bit in a 168-pin, dual read-out, single-in-line package comprising sixteen HYB 514400BJ/BT 1M × 4 DRAMs in 300 mil wide SOJ or TSOPII - packages mounted together with sixteen 0.2 μF ceramic decoupling capacitors on a PC board. All inputs except RAS and DQ are buffered by using four BiCMOS 8-bit buffers/line drivers.

Each HYB 514400BJ/BT is described in the data sheet and is fully electrically tested and processed according to Siemens standard quality procedure prior to module assembly. After assembly onto the board, a further set of electrical tests is performed.

The density and speed of the module can be detected by the use of presence detect pins.

Ordering Information

Type	Ordering Code	Package	Descriptions
HYM 641020GS-60	Q67100 - Q2003	L-DIM-168-1	60 ns DRAM module
HYM 641020GS-70	on request	L-DIM-168-1	70 ns DRAM module
HYM 641010GS-60	Q67100 - Q2002	L-DIM-168-1	60 ns DRAM module
HYM 641010GS-70	on request	L-DIM-168-1	70 ns DRAM module

Pin Names

A0-A9,B0	Address Input
DQ0 - DQ63	Data Input/Output
RAS0, RAS2	Row Address Strobe
CAS0 - CAS7	Column Address Strobe
WE0, WE2	Read / Write Input
OE0, OE2	Output Enable
Vcc	Power (+5 Volt)
Vss	Ground
PD1 - PD8	Presence Detect Pins
PDE	Presence Detect Enable
ID0 , ID1	ID identification bit
N.C.	No Connection

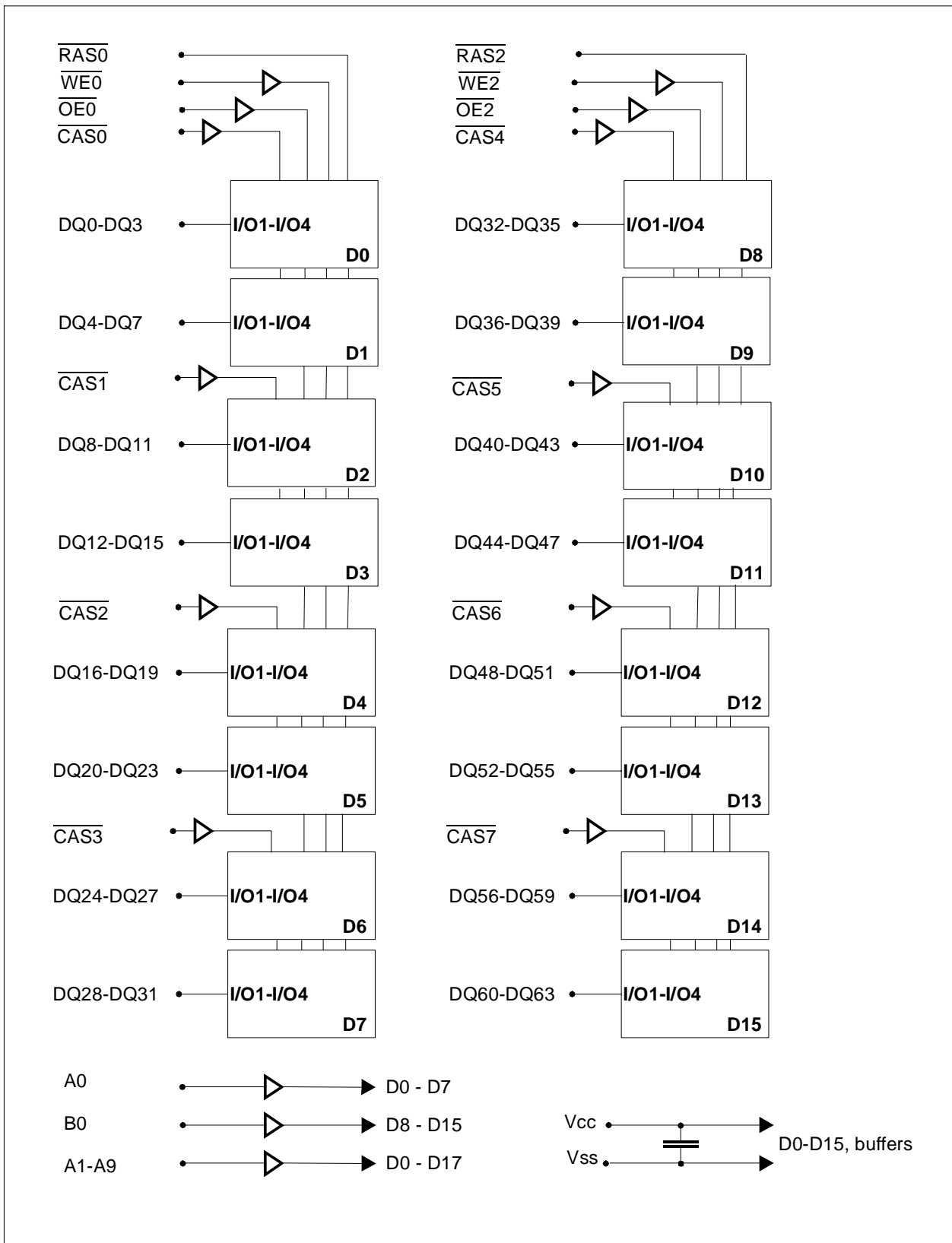
Presence-Detect and ID-pin Truth Table:

Module	ID0	ID1	PD1	PD2	PD3	PD4	PD5	PD6	PD7	PD8
HYM 641010/20GS-60	Vss	Vss	0	0	1	0	0	1	1	1
HYM 641010/20GS-70	Vss	Vss	0	0	1	0	0	0	1	1

Note: 1 = high level (driver output), 0 = low level (driver output) for \overline{PDE} active (ground) . For \overline{PDE} at a high level all PD terminals are in tri-state.

Pin Configuration

PIN #	Symbol	PIN #	Symbol	PIN #	Symbol	PIN #	Symbol
1	VSS	43	VSS	85	VSS	127	VSS
2	DQ0	44	OE2	86	DQ32	128	NC
3	DQ1	45	RAS2	87	DQ33	129	NC
4	DQ2	46	CAS4	88	DQ34	130	CAS5
5	DQ3	47	CAS6	89	DQ35	131	CAS7
6	VCC	48	WE2	90	VCC	132	PDE
7	DQ4	49	VCC	91	DQ36	133	VCC
8	DQ5	50	NC	92	DQ37	134	NC
9	DQ6	51	NC	93	DQ38	135	NC
10	DQ7	52	DQ16	94	DQ39	136	DQ48
11	NC	53	DQ17	95	NC	137	DQ49
12	VSS	54	VSS	96	VSS	138	VSS
13	DQ8	55	DQ18	97	DQ40	139	DQ50
14	DQ9	56	DQ19	98	DQ41	140	DQ51
15	DQ10	57	DQ20	99	DQ42	141	DQ52
16	DQ11	58	DQ21	100	DQ43	142	DQ53
17	DQ12	59	VCC	101	DQ44	143	VCC
18	VCC	60	DQ22	102	VCC	144	DQ54
19	DQ13	61	NC	103	DQ45	145	NC
20	DQ14	62	NC	104	DQ46	146	NC
21	DQ15	63	NC	105	DQ47	147	NC
22	NC	64	NC	106	NC	148	NC
23	VSS	65	DQ23	107	VSS	149	DQ55
24	NC	66	NC	108	NC	150	NC
25	NC	67	DQ24	109	NC	151	DQ55
26	VCC	68	VSS	110	VCC	152	VSS
27	WE0	69	DQ25	111	NC	153	DQ57
28	CAS0	70	DQ26	112	CAS1	154	DQ58
29	CAS2	71	DQ27	113	CAS3	155	DQ59
30	RAS0	72	DQ28	114	NC	156	DQ60
31	OE0	73	VCC	115	NC	157	VCC
32	VSS	74	DQ29	116	VSS	158	DQ61
33	A0	75	DQ30	117	A1	159	DQ62
34	A2	76	DQ31	118	A3	160	DQ63
35	A4	77	NC	119	A5	161	NC
36	A6	78	VSS	120	A7	162	VSS
37	A8	79	PD1	121	A9	163	PD2
38	NC	80	PD3	122	NC	164	PD4
39	NC	81	PD5	123	NC	165	PD6
40	VCC	82	PD7	124	VCC	166	PD8
41	NC	83	ID0	125	NC	167	ID1
42	NC	84	VCC	126	B0	168	VCC



Block Diagram

Absolute Maximum Ratings

Operating temperature range	0 to + 70 °C
Storage temperature range.....	- 55 to + 125 °C
Input/output voltage	- 1 to + 7 V
Power supply voltage.....	- 1 to + 7 V
Power dissipation.....	12,32 W
Data out current (short circuit)	50 mA

Note: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC Characteristics ¹⁾

$T_A = 0$ to 70 °C; $V_{CC} = 5$ V \pm 10 %

Parameter	Symbol	Limit Values		Unit	Test Condition
		min.	max.		
Input high voltage	V_{IH}	2.4	5.5	V	–
Input low voltage	V_{IL}	- 1.0	0.8	V	–
Output high voltage ($I_{OUT} = - 5$ mA)	V_{OH}	2.4	–	V	–
Output low voltage ($I_{OUT} = 4.2$ mA)	V_{OL}	–	0.4	V	–
Input leakage current (0 V < $V_{IN} < 6.5$ V, all other pins = 0 V)	$I_{I(L)}$	- 10	10	μ A	–
Output leakage current (DO is disabled, 0 V < $V_{OUT} < 5.5$ V)	$I_{O(L)}$	- 10	10	μ A	–
Average V_{CC} supply current: HYM 641010/20GS-60 HYM 641010/20GS-70 (\overline{RAS} , \overline{CAS} , address cycling, $t_{RC} = t_{RC}$ min.)	I_{CC1}	–	1760 1600	mA mA	2), 3)
Standby V_{CC} supply current ($\overline{RAS} = \overline{CAS} = V_{IH}$)	I_{CC2}	–	50	mA	–
Average V_{CC} supply current during \overline{RAS} only refresh cycles: HYM 641010/20GS-60 HYM 641010/20GS-70 (\overline{RAS} cycling, $\overline{CAS} = V_{IH}$, $t_{RC} = t_{RC}$ min.)	I_{CC3}	–	1760 1600	mA mA	2)

DC Characteristics (cont'd) ¹⁾

Parameter	Symbol	Limit Values		Unit	Test Condition
		min.	max.		
Average V_{CC} supply current during fast page mode: HYM 641010/20GS-60 HYM 641010/20GS-70 ($\overline{RAS} = V_{IL}$, \overline{CAS} , address cycling $t_{PC} = t_{PC \text{ min.}}$)	I_{CC4}	– –	1120 1120	mA mA	2), 3)
Standby V_{CC} supply current ($\overline{RAS} = \overline{CAS} = V_{CC} - 0.2 \text{ V}$)	I_{CC5}	–	30	mA	–
Average V_{CC} supply current during CAS-before-RAS refresh mode: HYM 641010/20GS-60 HYM 641010/20GS-70 (\overline{RAS} , \overline{CAS} cycling, $t_{RC} = t_{RC \text{ min.}}$)	I_{CC6}	– –	1760 1600	mA mA	1)

Capacitance

$T_A = 0 \text{ to } 70 \text{ }^\circ\text{C}$; $V_{CC} = 5 \text{ V} \pm 10 \%$; $f = 1 \text{ MHz}$

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Input capacitance (A0 to A9,B0)	C_{11}	–	10	pF
Input capacitance ($\overline{RAS0}$, $\overline{RAS2}$)	C_{12}	–	50	pF
Input capacitance ($\overline{CAS0}$ - $\overline{CAS7}$)	C_{13}	–	15	pF
Input capacitance ($\overline{WE0}$, $\overline{WE2}$, $\overline{OE0}$, $\overline{OE2}$)	C_{14}	–	15	pF
I/O capacitance (DQ0-DQ63)	C_{101}	–	15	pF

AC Characteristics (note: 5,6,7,8)

$T_A = 0$ to 70 °C, $V_{CC} = 5.0 \pm 10\%$

Parameter	Symbol	-60		-70		Unit	Note
		min.	max.	min.	max.		
common parameters							
Random read or write cycle time	t_{RC}	110	–	130	–	ns	
RAS precharge time	t_{RP}	40	–	50	–	ns	
RAS pulse width	t_{RAS}	60	100k	70	100k	ns	
\overline{CAS} pulse width	t_{CAS}	15	100k	20	100k	ns	
\overline{CAS} precharge time	t_{CP}	10	–	10	–	ns	
Row address setup time	t_{ASR}	5	–	5	–	ns	9
Row address hold time	t_{RAH}	8	–	8	–	ns	10
Column address setup time	t_{ASC}	2	–	2	–	ns	11
Column address hold time	t_{CAH}	15	–	20	–	ns	9
\overline{RAS} to \overline{CAS} delay time	t_{RCD}	18	40	18	45		12
\overline{RAS} to column address delay time	t_{RAD}	13	25	13	30	ns	12
\overline{RAS} hold time	t_{RSH}	20	–	25	–	ns	9
\overline{CAS} hold time	t_{CSH}	58	–	68	–	ns	10
\overline{CAS} to \overline{RAS} precharge time	t_{CRP}	10	–	10	–	ns	9
Transition time (rise and fall)	t_T	3	30	3	30	ns	7
Refresh period	t_{REF}	–	16	–	16	ms	

Read Cycle

Access time from \overline{RAS}	t_{RAC}	–	60	–	70	ns	13,14
Access time from \overline{CAS}	t_{CAC}	–	20	–	25	ns	9,13,14
Access time from column address	t_{AA}	–	35	–	40	ns	9,13,15
\overline{OE} access time	t_{OEA}	–	20	–	25	ns	9,13
Column address to \overline{RAS} lead time	t_{RAL}	35	–	40	–	ns	9
Read command setup time	t_{RCS}	2	–	2	–	ns	11
Read command hold time	t_{RCH}	2	–	2	–	ns	11,16
Read command hold time referenced to \overline{RAS}	t_{RRH}	0	–	0	–	ns	16
\overline{CAS} to output in low-Z	t_{CLZ}	2	–	2	–	ns	11,13
Output buffer turn-off delay	t_{OFF}	–	20	–	25	ns	9,17
Output buffer turn-off delay from \overline{OE}	t_{OEZ}	–	20	–	25	ns	9,17

AC Characteristics (cont'd)(note: 5,6,7,8)

$T_A = 0$ to 70 °C, $V_{CC} = 5.0 \pm 10\%$

Parameter	Symbol	-60		-70		Unit	Note
		min.	max.	min.	max.		
CAS delay time from Din	t_{DZC}	0	–	0	–	ns	18
Data to \overline{OE} low delay	t_{DZO}	0	–	0	–	ns	18
\overline{CAS} high to data delay	t_{CDD}	20	–	25	–	ns	9,19
\overline{OE} high to data delay	t_{ODD}	20	–	25	–	ns	9,19

Write Cycle

Write command hold time	t_{WCH}	15	–	15	–	ns	9
Write command pulse width	t_{WP}	10	–	10	–	ns	
Write command setup time	t_{WCS}	2	–	2	–	ns	11,20
Write command to \overline{RAS} lead time	t_{RWL}	20	–	25	–	ns	9
Write command to \overline{CAS} lead time	t_{CWL}	15	–	20	–	ns	
Data setup time	t_{DS}	-2	–	-2	–	ns	10,21
Data hold time	t_{DH}	15	–	20	–	ns	9,21

Read-Modify-Write Cycle

Read-write cycle time	t_{RWC}	155	–	185	–	ns	9
\overline{RAS} to \overline{WE} delay time	t_{RWD}	82	–	97	–	ns	11,21
\overline{CAS} to \overline{WE} delay time	t_{CWD}	37	–	47	–	ns	11,21
Column address to \overline{WE} delay time	t_{AWD}	52	–	62	–	ns	11,21
\overline{OE} command hold time	t_{OEH}	13	–	18	–	ns	10

Fast Page Mode Cycle

Fast page mode cycle time	t_{PC}	40	–	45	–	ns	
Access time from \overline{CAS} precharge	t_{CPA}	–	40	–	45	ns	9,13
\overline{RAS} pulse width	t_{RAS}	60	200k	70	200k	ns	
\overline{CAS} precharge to \overline{RAS} Delay	t_{RHCP}	40	–	45	–	ns	9

AC Characteristics (cont'd)(note: 5,6,7,8)

$T_A = 0$ to 70 °C, $V_{CC} = 5.0 \pm 10\%$

Parameter	Symbol	-60		-70		Unit	Note
		min.	max.	min.	max.		

Fast Page Mode Read-Modify-Write Cycle

Fast page mode read-write cycle time	t_{PRWC}	82	–	97	–	ns	11
\overline{CAS} precharge to \overline{WE}	t_{CPWD}	57	–	67	–	ns	11,21

\overline{CAS} -before- \overline{RAS} Refresh Cycle

\overline{CAS} setup time	t_{CSR}	12	–	12	–	ns	11
\overline{CAS} hold time	t_{CHR}	8	–	8	–	ns	10
\overline{RAS} to \overline{CAS} precharge time	t_{RPC}	5	–	5	–	ns	
Write to \overline{RAS} precharge time	t_{WRP}	12	–	12	–	ns	11
Write hold time referenced to \overline{RAS}	t_{WRH}	8	–	8	–	ns	10

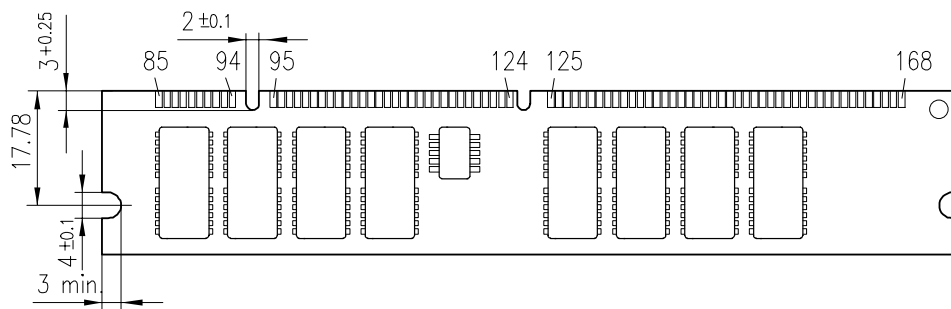
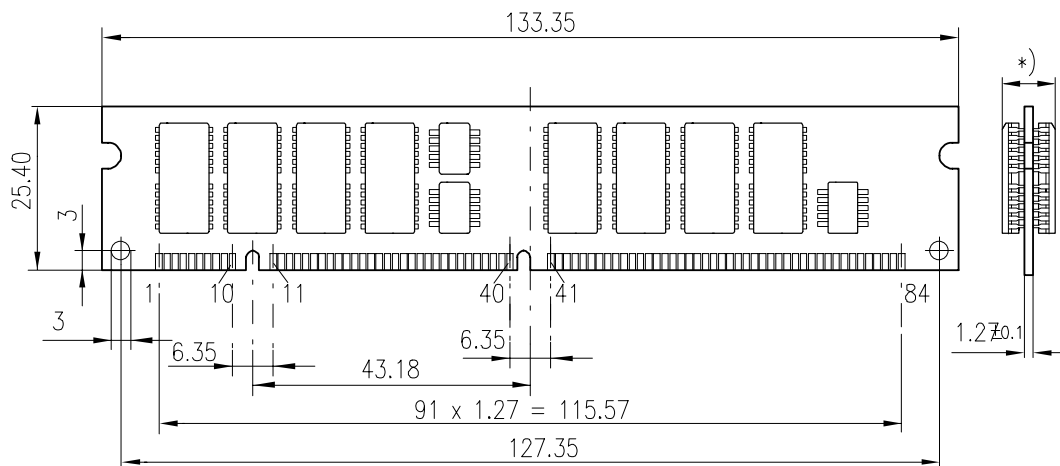
Presence Detect Read Cycle

\overline{PDE} to valid presence detect data	t_{PD}	–	10			ns	
\overline{PDE} inactive to presence detects inactive	t_{PDOFF}	0	10			ns	

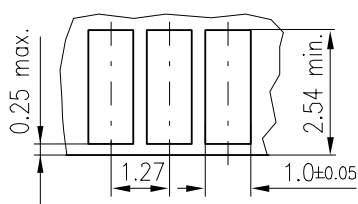
Notes:

- 1) All voltages are referenced to VSS.
- 2) ICC1, ICC3, ICC4 and ICC6 and ICC7 depend on cycle rate.
- 3) ICC1 and ICC4 depend on output loading. Specified values are measured with the output open.
- 4) Address can be changed once or less while $\overline{\text{RAS}} = \text{Vil}$. In the case of ICC4 it can be changed once or less during a fast page mode cycle (tpc).
- 5) An initial pause of 100 μs is required after power-up followed by 8 RAS-only-refresh cycles, before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 $\overline{\text{CAS}}$ -before-RAS initialization cycles instead of 8 $\overline{\text{RAS}}$ cycles are required.
- 6) AC measurements assume $t_T = 5 \text{ ns}$.
- 7) VIH (min.) and VIL (max.) are reference levels for measuring timing of input signals. Also, transition times are measured between VIH and VIL .
- 8) The specified timings include buffer, loading and skew delay adders: 2ns minimum, 5ns ($\overline{\text{CAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$, addresses) maximum delay, no pulse shrinkage to the DRAM device timings. The data and RAS signals are not buffered, which preserves the DRAMs access specification of 50ns and 60ns.
- 9) A +5ns timing skew from the DRAM to the module resulted from the addition of line drivers.
- 10) A -2ns timing skew from the DRAM to the module resulted from the addition of line drivers.
- 11) A +2ns timing skew from the DRAM to the module resulted from the addition of line drivers.
- 12) A -2ns (min.) and a -5ns (max.) timing skew from the DRAM to the module resulted from the addition of line drivers.
- 13) Measured with the specified current load and 100 pF at $\text{Voh} = 2.4 \text{ V}$ and $\text{Vol} = 0.4 \text{ V}$.
- 14) Operation within the t_{RCD} (max.) limit ensures that t_{RAC} (max.) can be met. t_{RCD} (max.) is specified as a reference point only: If t_{RCD} is greater than the specified t_{RCD} (max.) limit, then access time is controlled by t_{CAC} .
- 15) Operation within the t_{RAD} (max.) limit ensures that t_{RAC} (max.) can be met. t_{RAD} (max.) is specified as a reference point only: If t_{RAD} is greater than the specified t_{RAD} (max.) limit, then access time is controlled by t_{AA} .
- 16) Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
- 17) t_{OFF} (max.) and t_{OEZ} (max.) define the time at which the outputs achieve the open-circuit condition and are not referenced to output voltage levels.
- 18) Either t_{DZC} or t_{DZO} must be satisfied.
- 19) Either t_{CDD} or t_{ODD} must be satisfied.
- 20) t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{\text{WCS}} > t_{\text{WCS}}(\text{min.})$, the cycle is an early write cycle and the I/O pin will remain open-circuit (high impedance) through the entire cycle; if $t_{\text{RWD}} > t_{\text{RWD}}(\text{min.})$, $t_{\text{CWD}} > t_{\text{CWD}}(\text{min.})$, $t_{\text{AWD}} > t_{\text{AWD}}(\text{min.})$ and $t_{\text{CPWD}} > t_{\text{CPWD}}(\text{min.})$, the cycle is a read-write cycle and I/O pins will contain data read from the selected cells. If neither of the above sets of conditions is satisfied, the condition of the I/O pins (at access time) is indeterminate.
- 21) These parameters are referenced to $\overline{\text{CAS}}$ leading edge in early write cycles and to $\overline{\text{WE}}$ leading edge in Read-Modify-Write cycles.

L-DIM-168-1
Module package
(dual read-out, single in-line memory module)



Detail of Contacts



*) 8.89 max. for modules assembled with P-SOJ-devices
4.06 max. for modules assembled with P-TSOPII-devices

GLD05860